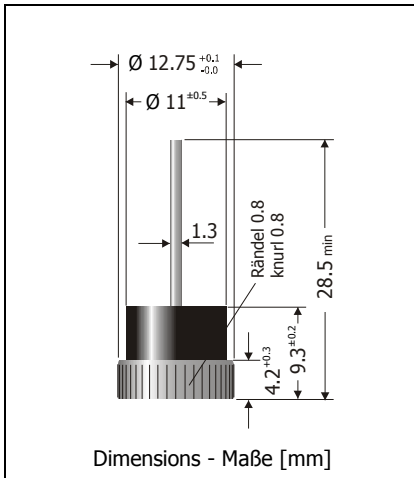


BYP25A05 ... BYP25A6, BYP25K05 ... BYP25K6

**Silicon-Press-Fit-Diodes – High Temperature Diodes
Silizium-Einpress-Dioden – Hochtemperatur-Dioden**

Version 2014-08-18



Nominal Current 25 A
 Nennstrom
 Repetitive peak reverse voltage 50 ... 600 V
 Periodische Spitzensperrspannung
 Metal press-fit case with plastic cover
 Metall-Einpressgehäuse mit Plastik-Abdeckung
 Weight approx. 10 g
 Gewicht ca.
 Compound has classification UL94V-0
 Vergussmasse nach UL94V-0 klassifiziert
 Standard packaging: bulk
 Standard Lieferform: lose im Karton



Maximum ratings

Grenzwerte

Type / Typ Wire to / Draht an		Repetive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V]	Surge peak reverse voltage Stoßspitzensperrspannung V_{RSM} [V]
Anode	Cathode		
BYP25A05	BYP25K05	50	60
BYP25A1	BYP25K1	100	120
BYP25A2	BYP25K2	200	240
BYP25A3	BYP25K3	300	360
BYP25A4	BYP25K4	400	480
BYP25A6	BYP25K6	600	700

Max. average forward rectified current, R-load Dauergrenzstrom in Einwegschaltung mit R-Last	$T_C = 150^\circ\text{C}$	I_{FAV}	25 A
Repetitive peak forward current Periodischer Spitzenstrom	$f > 15\text{ Hz}$	I_{FRM}	90 A ¹⁾
Peak forward surge current, 50/60 Hz half sine-wave Stoßstrom für eine 50/60 Hz Sinus-Halbwelle	$T_A = 25^\circ\text{C}$	I_{FSM}	270/300 A
Rating for fusing, $t < 10\text{ ms}$ Grenzlastintegral, $t < 10\text{ ms}$	$T_A = 25^\circ\text{C}$	i^2t	375 A ² s
Operating junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur		T_j T_s	-50...+215°C -50...+215°C

1 Max. case temperature $T_C = 150^\circ\text{C}$ – Max. Gehäusetemperatur $T_C = 150^\circ\text{C}$

Characteristics
Kennwerte

Forward Voltage Durchlass-Spannung	$T_j = 25^\circ\text{C}$ $I_F = 25\text{ A}$	V_F	< 1.1 V
Leakage Current Sperrstrom	$T_j = 25^\circ\text{C}$ $V_R = V_{RRM}$	I_R	< 100 μA
Thermal Resistance Junction – Case Wärmewiderstand Sperrschicht – Gehäuse		R_{thc}	< 1 K/W
Maximum pressing force Maximaler Einpressdruck		F_{pmax}	4 kN

